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Role of tilt grain boundaries on the structural integrity of WSe_2 monolayers†

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Transition metal dichalcogenides (TMDCs) are potential materials for future optoelectronic devices. Grain boundaries (GBs) can significantly influence the optoelectronic properties of TMDC materials. Here, we have investigated the mechanical characteristics of tungsten diselenide (WSe_2) monolayers and failure process with symmetric tilt GBs using ReaxFF molecular dynamics simulations. In particular, the effects of topological defects, loading rates, and temperatures are investigated. We considered nine different grain boundary structures of monolayer WSe_2, of which six are armchair (AC) tilt structures, and the remaining three are zigzag (ZZ) tilt structures. Our results indicate that both tensile strength and fracture strain of WSe_2 with symmetric tilt GBs decrease as the temperature increases. We revealed an interfacial phase transition for high-angle GBs reduces the elastic strain energy within the interface at finite temperatures. Furthermore, brittle cracking is the dominant failure mode in the WSe_2 monolayer with tilted GBs. WSe_2 GB structures showed more strain rate sensitivity at high temperatures than at low temperatures.

Introduction

Multi-layered materials have strong chemical bonds within the layer but weak van der Waals forces in between,[1] which allows these materials to be physically or chemically thinned to a single atomic two-dimensional (2D) layer.[2] The synthesis of 2D materials has become critical in modern materials research[3–13] because of their unique physicochemical properties that differ from their bulk counterparts. Specifically, these materials with defined geometries exhibit unique shape-dependent properties and have been successfully used in nanoelectronics devices.[14] In the 2D materials family, graphene is immensely popular because of its several unique features, such as thermal conductivity, visual transparency, and elastic properties[15–17] that motivated several studies investigating its mechanochemistry.[18–20] However, the absence of an electronic bandgap[21] has motivated a drive for synthesizing 2D materials with semiconducting capabilities, including TMDCs. These materials have attracted significant attention because of their natural abundance and semiconducting capabilities among 2D materials.[22]

Tungsten diselenide (WSe_2), a TMDC, is an excellent option for semiconducting applications.[23–27] It comprises one layer of W atoms sandwiched between two layers of Se atoms. Mechanical exfoliation[28,29] and chemical vapor deposition (CVD)[30–34] are the two main fabrication methods of WSe_2. Like all other materials, WSe_2 has a variety of defects, including edges, vacancies, adatoms, substitutional impurities, and GBs, all of which significantly impact its characteristics.[35–38] GBs are a common form of defect in large-scale 2D material films synthesized by CVD, significantly impacting their characteristics.[39] Several studies have been performed to understand the role of defects in the characteristics of various 2D materials. The mechanical properties of the pristine and air-aged high-quality WS_2, WSe_2, and WTe_2 were studied by the indentation method,[40] demonstrating that the mechanical properties of WS_2 degraded the most with thickness. The mechanical properties of graphene–WSe_2 vertical heterostructures were also studied using the MD technique,[41] indicating direction-dependent fracture processes, where the WSe_2 sheet transformed from h-WSe_2 to t-WSe_2 upon loading in the ZZ direction. In another study on MoS_2, it was shown that GBs and vacancy defects degrade the mechanical characteristics of MoS_2. In contrast, vacancy inclusion at a small scale promotes plasticity in MoS_2 and reduces the

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tensile strength.[42] MD simulations were also used to investigate the effects of temperature, strain rate, and vacancies on the mechanical responses of h-WSe_2 and t-WSe_2,[43] indicating strain rate independence of the fracture strain, fracture strength, and Young's modulus of both h-WSe_2 and t-WSe_2. Furthermore, upon increasing the density of vacancies, the mechanical strength of both h-WSe_2 and t-WSe_2 reduced due to the increase in the density of microcracks and disorganization of W–Se bonds.

Despite the aforementioned studies on the role of defects in 2D materials, a comprehensive study of the role of GBs on mechanical properties in the WSe_2 monolayer is lacking. This topic is of paramount importance because all the large-scale WSe_2 films are polycrystals. Thus, here we used ReaxFF MD simulations to investigate the role of tilt GBs on the mechanical characteristics of bi-crystal WSe_2 monolayers.

Methodology

We created ∼27 nm × ∼27 nm monolayer WSe_2 models containing symmetric AC tilt GBs of three different misorientation angles – *i.e.*, 9.4°, 13.2°, and 21.8° – as shown in Fig. 1. Unlike graphene, WSe_2 AC tilt GBs are of two types based on the bond shared by the pentagon-heptagon ring: (i) the Se–Se and (ii) the W–W bond shared pentagon-heptagon defects. They are identified as Se5|7 and W5|7, respectively. The Se–Se bond shared structures of the symmetric AC tilt GB and the W–W bond shared structures of the symmetric AC tilt GB for the three misorientation angles considered here are shown in Fig. 1(a–c) and (d–f), respectively. The considered ZZ tilt W5|7 + Se5|7 structures are shown in Fig. 1(g)–(i). GBs were generated by rotating a WSe_2 monolayer's unit cell at the necessary angle and converting it to its orthogonal cell. This structure was duplicated in the planer direction to reach ∼150 Å. Mirroring the structure created negative rotation. Stitching the two structures together and deleting duplicate atoms in the interface generated the GB.[44] Removing duplicate atoms from planar image cells validated the periodicity of the boundary structure.

We created the GB by rotating two monolayers at the same angle but in opposite directions, stitching them together, deleting the overlapped atoms in the structure, and minimizing energy using the conjugate gradient method. We used 0.65 nm as the nominal thickness of monolayer WSe_2 structures.[45] All the structures are periodic in the plane of the monolayer WSe_2 to avoid the finite-size effects.[46] ReaxFF MD simulations are used to investigate the mechanical properties and the fracture mechanism of the bi-crystal WSe_2 monolayer. We used the Large-scale Atomic/Molecular Massively Parallel Simulator (LAMMPS) code to perform the simulations[47] with a time step of 0.25 fs. Following the energy minimization, we relaxed the structures at simulation temperatures within the range of 10–300 K using the Nose–Hoover thermostat (*NVT*) for 12.5 ps and then using the Noose–Hoover barostat (*NPT*) for another 50 ps at atmospheric pressure and simulation temperatures ranging 10–300 K. Damping constant for temperature and pressure is 50 fs and 1250 fs, respectively. The standard velocity-Verlet integrator is used to integrate the equations of motion. The structure's (virial) stress–strain behaviour is obtained by deforming the simulation box perpendicular to the GB direction in the *NPT* ensemble with an engineering strain rate of 10^9 s^{-1} compatible with other MD studies.[48,49] As a result, the length of the simulation box along the GB was changed due to Poisson's effect.

We used modified ReaxFF potential[45] to capture covalent bond breaking and formation by updating the bond order at each MD timestep. We validated the model by calculating the properties of pristine AC and ZZ WSe_2 under the *NPT* ensemble at 300 K. We calculated Young's modulus of pristine ZZ and AC WSe_2 as 201 GPa and 225 GPa, respectively, which agrees with the reported values.[45] We calculated an ultimate strength of 22 GPa and 27 GPa for ZZ and AC WSe_2 monolayers, respectively, which are comparable to the 23.7 GPa and 28.4 GPa

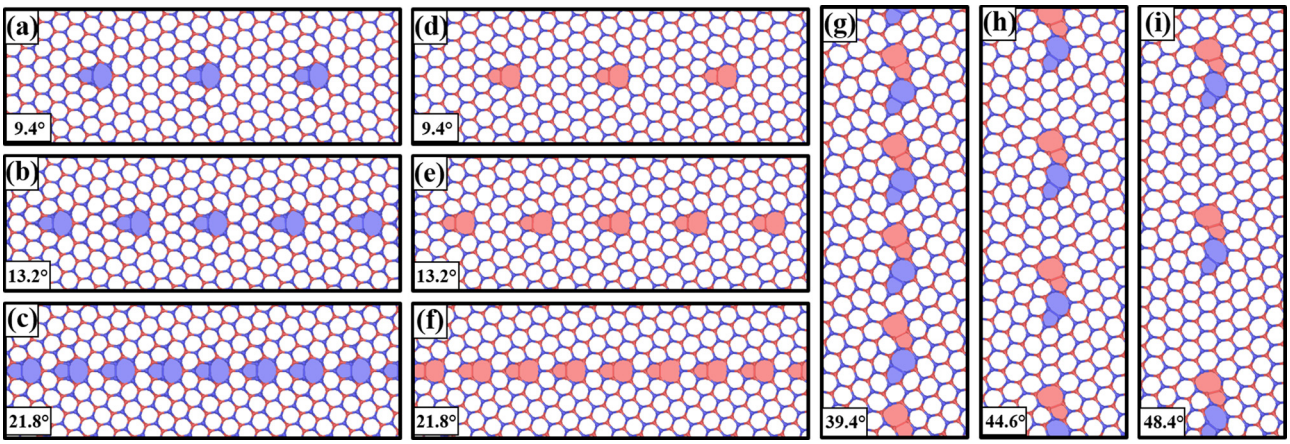

Fig. 1 Monolayer WSe_2 GB structures. Se5|7 dislocations in AC tilt GBs with tilt angles of (a) 9.4°, (b) 13.2°, and (c) 21.8°; W5|7 dislocations in AC tilt GBs with tilt angles of (d) 9.4°, (e) 13.2°, and (f) 21.8°; ZZ tilt GBs made up of W5|7 + Se5|7 dislocations with tilt angles of (g) 39.4°, (h) 44.6°, and (i) 48.4°. W5|7 and Se5|7 dislocations in GBs are coloured in red and blue, respectively. Red circles represent W atoms, and blue circles represent Se atoms.

values reported in the literature.[45] Young's modulus for the WSe_2 monolayer is found to be 201 GPa using density functional theory calculations that are also comparable to our analyses.[50] The stress–strain response for pristine WSe_2 is presented in Fig. S1 of the ESI.†

Results and discussion

Effect of internal stresses and strains

Failure of materials, including atomically thin WSe_2, is driven by the formation of microcracks, which are formed when stresses in the material increase beyond some critical stress, *e.g.*, von Mises stress.[51] Thus, internal stresses strongly impact the formation and propagation of microcracks and, thus, the final strength of materials. WSe_2 monolayers are no exception. GBs are the microstructural features altering the internal stresses and thus determine the final properties of monolayers. In contrast to the pristine WSe_2 monolayer structure, interatomic bond lengths are non-uniform in the tilt GB region, resulting in pre-strained bonds due to the presence of GB dislocations in the form of a pentagon-heptagon (5|7) pair. From a geometric point of view, a 5|7 pair looks like a disclination dipole, which has two disclinations of opposite signs.[52–54] The pentagon defect is considered positive disclination, and the heptagon is considered negative disclination.

Grain boundaries may consist of evenly spaced disclination dipoles or dipole clusters. Here, we considered the evenly spaced disclination dipoles for AC and ZZ tilt GBs. The stress-volume component normal to the GB is plotted in Fig. 2, *i.e.*, σ_{yy} for the AC tilt GB, Fig. 2(a)–(f), and σ_{xx} for the ZZ tilt GB, Fig. 2(g)–(i). These contour plots show a similar trend reported

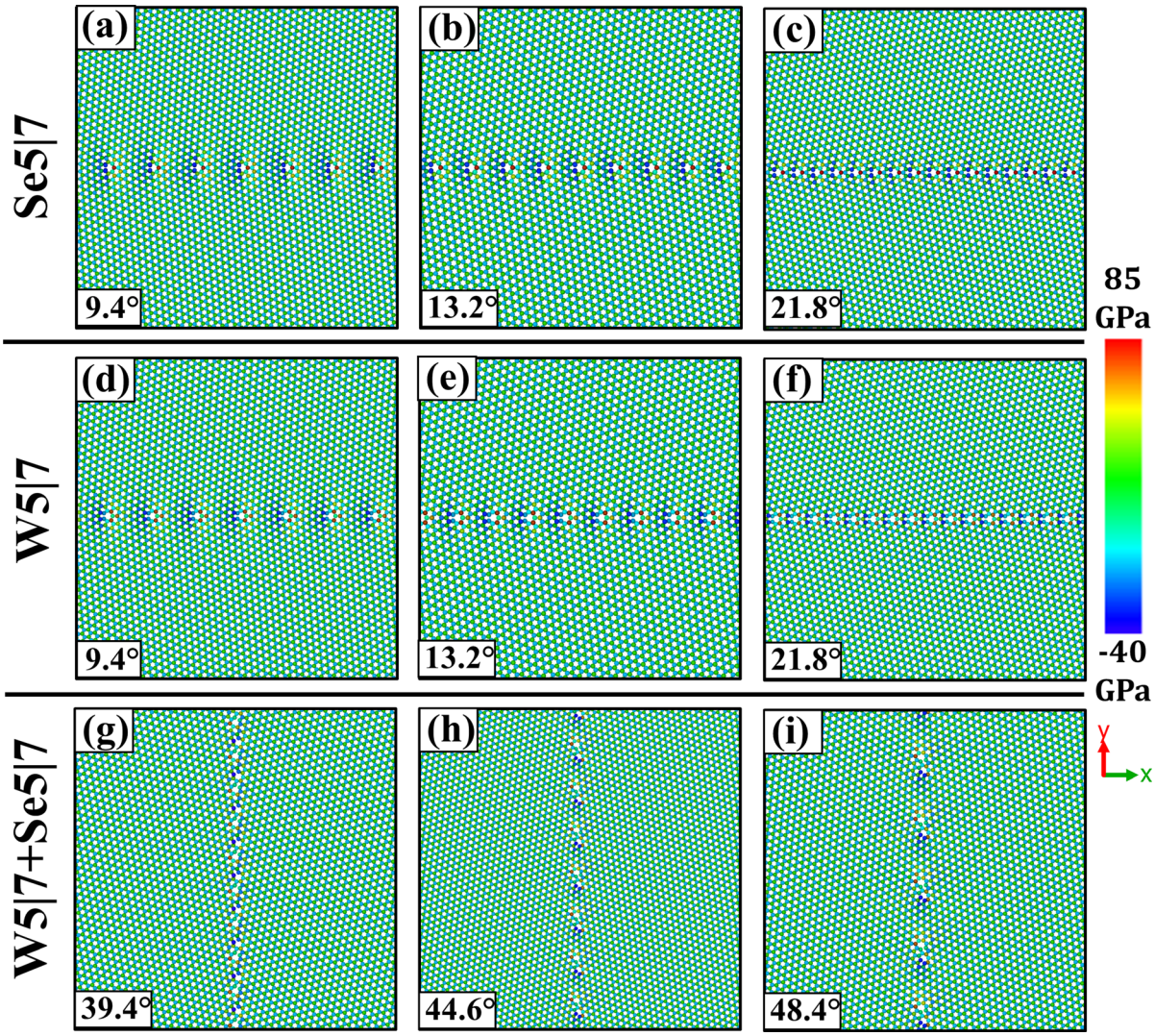

Fig. 2 Atomic pre-stress due to the presence of the WSe_2 GB. (a) 9.4° Se5|7, (b) 13.2° Se5|7, (c) 21.8° Se5|7, (d) 9.4°W5|7, (e) 13.2°W5|7, (f) 21.8°W5|7, (g) 39.4°W5|7 + Se5|7, (h) 44.6°W5|7 + Se5|7, and (i) 48.4°W5|7 + Se5|7. For Se5|7, the maximum compressive stress is experienced by the Se–Se bond; for W5|7, the W–W bond experiences the maximum compressive stress. Color-coded plots are generated by plotting per-atom stress in the normal to GB direction.

for graphene GBs.[55] The stress volume unit is used here to avoid dealing with the controversies that may arise regarding the definition of volume for atomically thin structures. Compared to the hexagon ring bond length, the heptagon ring bonds are stretched, thus subjected to tensile stress, and the pentagon ring bonds are contracted and thus are subjected to compressive stress. Though several bonds are pre-stressed, the bond shared by the 5|7 ring experiences maximum compressive stress regardless of the misorientation angle. For Se5|7, the maximum compressive stress is experienced by the Se–Se bond, and maximum tensile stress is experienced by a single W atom of a heptagon, which has the longest distance from its nearest pentagon. For W5|7, the maximum compressive stress is experienced by the W–W bond, and maximum tensile stress is experienced by the double W atom of the heptagon. However, for graphene 5|7 dislocations, maximum stress was experienced by the bond shared by the hexagon and heptagon ring [44].

Effect of grain boundary

We have investigated the role of different GBs on the strength of bi-crystalline WSe_2 structures at low temperatures, where the effect of thermal fluctuations is negligible. The stress normal to GBs *vs.* strain response of the structures is shown in Fig. 3 for the AC tilt and ZZ tilt GBs at 10 K. We used three separate tensile loading simulations with different seed velocities for each GB to capture the correct statistics. Our simulations indicate an almost linear stress–strain correlation up to a critical point followed by a sudden drop in the finite strain regime, which is a brittle fracture characteristic.

The tensile strength of graphene sheets is higher for GBs with higher misorientation angles.[56,57] However, this behaviour was not observed[46] in a single-layer boron nitride nanosheet with tilted GBs. Here, for Se5|7 structures, the strength of low-angle GBs, *i.e.*, 9.4° and 13.2°, are relatively the same, while it suddenly drops for the 21.8° GB. The same conclusion can be made on the ZZ tilt W5|7 + Se5|7 structures. For the W5|7 structures, the strength is ordered as 21.8° > 13.2° > 9.4°, *i.e.*, there is a monotonic increase in strength with the misorientation. It indicates that the strength increases upon increasing the dislocation density, as the misorientation angle is correlated with the dislocation density. Dislocation density is maximum for the 21.8° GB structure and minimum for the 9.4° GB structure for both the Se5|7 and W5|7 AC tilt GB structures, Fig. 1.

For the ZZ tilt W5|7 + Se5|7 structures, dislocation density is maximum for the 39.4° structure and minimum for the 48.4° structure, Fig. 1. With increasing dislocation density, the gap between disclination dipoles reduces. Thus, the stress field for one disclination dipole interferes with the stress field of the adjacent disclination dipole, resulting in a higher elastic energy density that alters the mechanical response of the material. However, by computing the stress–strain curves for different misoriented GBs in Fig. 1, we can conclude that dislocation density is less critical in determining WSe_2's mechanical properties than the GB chemistry. Although the Se5|7 GB with higher dislocation density has the lowest fracture strain, the same W5|7 GB has the highest fracture strain. In the case of W5|7 + Se5|7 GB, the fracture stress is comparable with Se5|7 GB, which has the lowest fracture stress among Se5|7 and W5|7 GBs. It indicates that the strength of the GBs in WSe_2 is determined by the chemistry of the GB rather than dislocation density, where weaker bonds act as the bottleneck for the GB strength. We revealed the same trend in this work for Se5|7 and W5|7 GBs as to the AC tilt GB fracture strength of MoS_2 for S5|7 and Mo5|7 GB, respectively.[58]

The strain energy density (energy per atom), ψ^*, *vs.* strain at 10 K is shown in Fig. 4. Strain energy density is calculated as, ψ^* = (Total Energy − Initial Total Energy)/(No. of atoms), which follows a parabolic increase that is characteristic of a linear elastic deformation before reaching a maximum right before the sudden drop due to the breaking of bonds. The W5|7 structures are also demonstrating a higher rigidity compared to the Se5|7 counterparts, where ψ^* of W5|7 monolayers are twice as large as the Se5|7 structures.

Effect of temperature

We performed tensile test simulations at 10 K, 100 K, 200 K, and 300 K to understand the effect of temperature on the mechanical behaviour of WSe_2 structures with different GBs. The stress–strain curves for all the structures at the selected temperatures are shown in Fig. S2–S4 in the ESI.† Variations of fracture strength, σ_f, and fracture strain, ε_f, with temperature

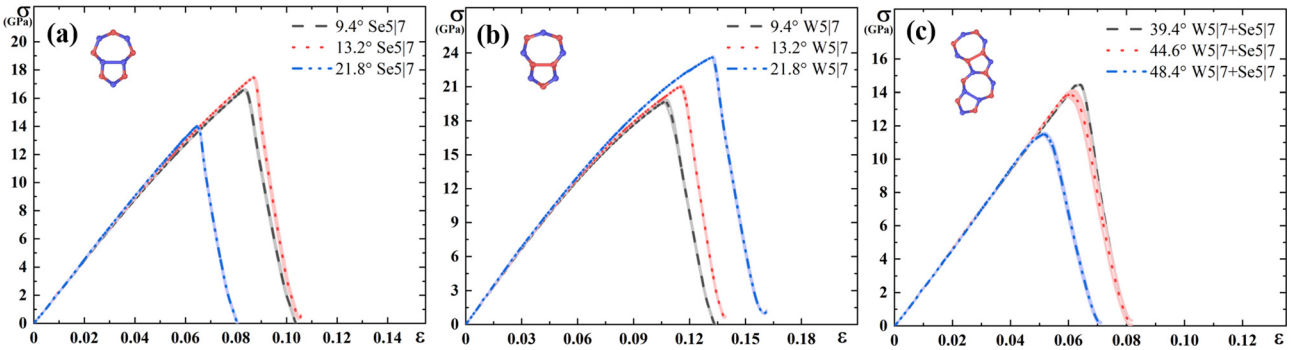

Fig. 3 Stress (σ)–strain (ε) response of differently misoriented grains under uniaxial loading normal to GB direction at 10 K temperature. (a) AC tilt Se5|7 structures, (b) AC tilt W5|7 structures, and (c) ZZ tilt W5|7 + Se5|7 structures. Red circles represent W atoms, and blue circles represent Se atoms.

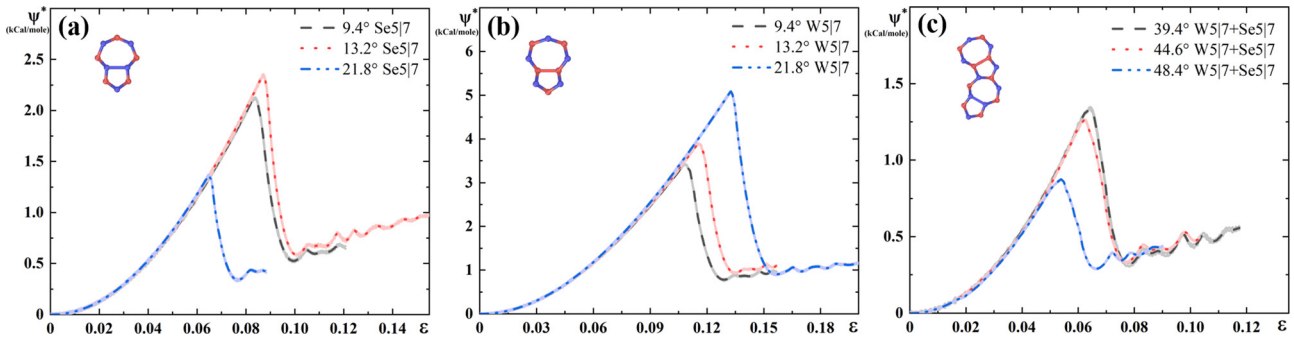

Fig. 4 Strain energy per atom, ψ^* (kcal mol^{-1}), *vs.* strain (ε) for differently misoriented structures at 10 K temperature. (a) AC tilt Se5|7 structures, (b) AC tilt W5|7 structures, and (c) ZZ tilt W5|7 + Se5|7 structures. Red circles represent W atoms, and blue circles represent Se atoms.

are shown in Fig. 5 for the AC tilt Se5|7 and W5|7, and ZZ tilt W5|7 + Se5|7 structures. We observed that σ_f and ε_f reduced for all the GB structures upon increasing temperature. The effect of temperature on σ_f and ε_f follows a similar trend reported for bigrain[59] and pristine[60] graphene. This behaviour can be explained by the thermally activated debonding process, where the thermal fluctuation energy contributes to the energy necessary for the nucleation and propagation of microcracks.

The effect of temperature on Young's modulus, E, is shown in Fig. 6 for the AC tilt Se5|7 and W5|7 GBs, and ZZ tilt W5|7 + Se5|7 GBs. Our results indicate a weak correlation between Young's modulus and temperature for the AC tilt Se5|7 structures compared to the W5|7 structures. There is not a statistically significant difference between E values of differently misoriented GBs at various temperatures (Fig. 6(a)). However, in the case of W5|7 GBs, the 9.4° GB has the lowest E value at all temperatures. There is no statistically meaningful difference between 13.2° and 21.8° W5|7 GBs beyond 100 K. Furthermore, the 9.4° Se5|7 and W5|7 GBs have the relatively same elastic modulus, while 13.2° and 21.8° W5|7 GBs have a higher Young's modulus compared with the corresponding Se5|7 GBs.

In the case of high-angle W5|7 + Se5|7 mixed GBs, we revealed a complex variation in E at different temperatures. Although E drops upon increasing temperature for all the considered high-angle GBs, the rate of reduction in the elastic modulus is different for each GB. Among the three GBs, the 46.4° W5|7 + Se5|7 GB has the largest drop in E upon increasing temperature greater than 100 K, which remains statistically constant up to room temperature. This drop is due to the structural change of GBs at high temperatures, shown in the Fig. S7 (ESI†). Increasing temperature for the high-angle GBs (44.6° and 48.4°) results in the dissociation of two adjacent 5|7 dislocations into separated intermediate 8|6 dislocations, followed by transformation into a tetragonal and horizontal 5|7 dislocation pair. This transformation allows the sharp angle in the high-angle bi-grain structure to split into two low-angle boundaries with a large angle between the crystals within the GB width, resulting in the relaxation of the interfacial stresses. The lowest rate of softening *vs.* temperature is for the 39.4° W5|7 + Se5|7 GB. Although it has the lowest E value at 10 K, it becomes the stiffest structure at room temperature. The calculated Young's modulus E of these structures is consistent with reported values.[45,50,61] In fact, Young's modulus for the pristine WSe_2 and the structures having different GB misorientations lies in the same, indicating the GBs do not impact Young's modulus.

Effect of the strain rate

The strain rate is a crucial factor in determining the mechanical properties of materials. Although the classical MD technique is inherently limited to very high strain rates, yet it can provide

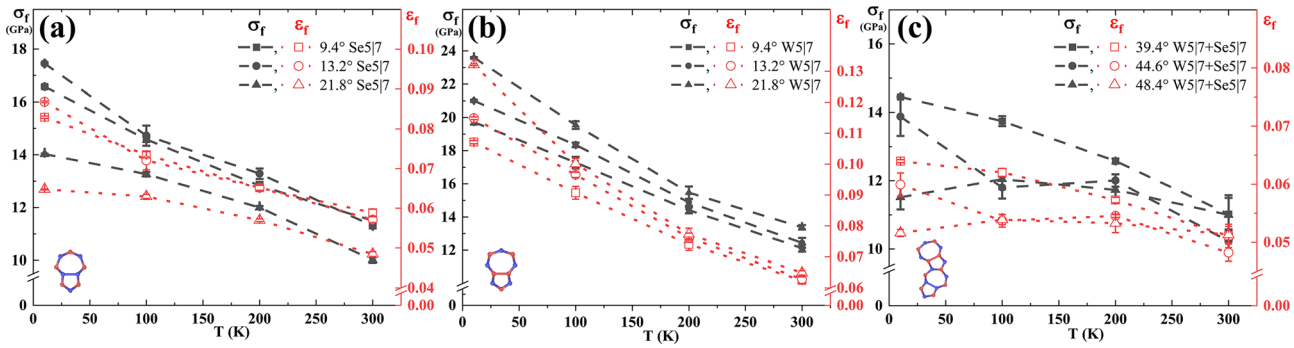

Fig. 5 Effect of temperature on the fracture strength (σ_f) and fracture strain (ε_f) for different GB structures. (a) AC tilt Se5|7 GBs with misorientation angle of 9.4°, 13.2°, 21.8°, (b) AC tilt W5|7 GBs with misorientation angle of 9.4°, 13.2°, 21.8°, and (c) ZZ tilt W5|7 + Se5|7 GBs with misorientation angles of 39.4°, 44.6°, 48.4°. The black and red lines indicate the fracture strength and strain curves with temperature, respectively. Red circles represent W atoms, and blue circles represent Se atoms.

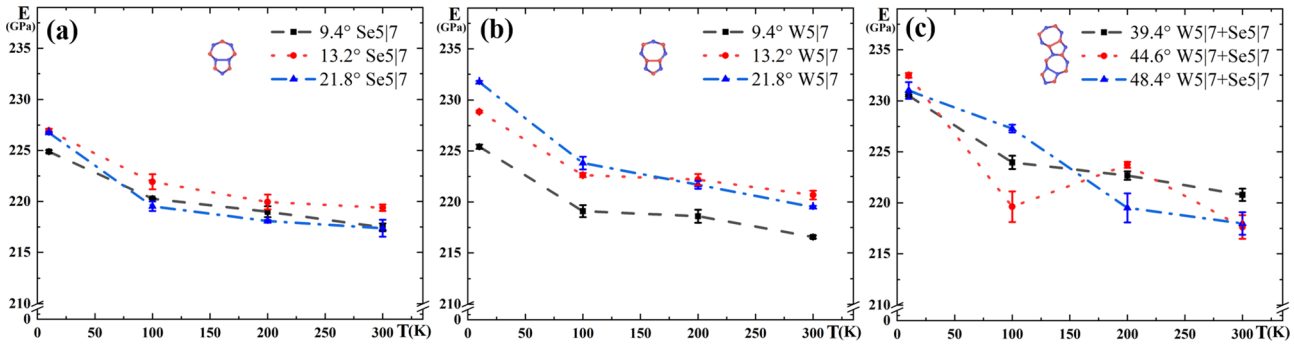

Fig. 6 Effect of temperature on Young's modulus for different GB structures. (a) AC tilt Se5|7 structures with misorientation angles of 9.4°, 13.2°, 21.8°, (b) AC tilt W5|7 structures with misorientation angles of 9.4°, 13.2°, 21.8°, and (c) ZZ tilt W5|7 + Se5|7 structures with misorientation angles of 39.4°, 44.6°, 48.4°.

insight into the mechanical behaviour of the material upon considering different strain rates. We performed uniaxial tensile test simulations at different strain rates to address the effect of strain rate sensitivity, for the AC tilt W5|7 GB with 9.4° misorientation angle at 10 K, 100 K, 200 K, 300 K, and 350 K. The strain rates selected for these simulations are 10^8 s^{-1}, 5×10^8 s^{-1}, 10^9 s^{-1}, and 5×10^9 s^{-1}. Statistical results are obtained by running three sets of simulations at the same temperature with different seed velocities.

The effect of strain rate on the strength of the material is evaluated using an Arrhenius type equation:[62]

$$\dot{\varepsilon} = A\sigma^{\frac{1}{m}} e^{-\frac{Q}{RT}} \tag{1}$$

Here, m is the strain rate sensitivity, A is a constant, and R is the universal gas constant r. $\dot{\varepsilon}$, σ, Q, and T are the strain rate, fracture strength, activation energy, and temperature, respectively. From eqn (1), by taking the natural logarithm, we have

$$\ln(\dot{\varepsilon}) = \ln(A) + \frac{1}{m}\ln(\sigma) - \frac{Q}{RT}. \tag{2}$$

Partial differentiation of eqn (2) assuming T as a constant, as the simulations were performed at controlled temperatures, we have

$$m = \frac{\partial \ln(\sigma)}{\partial \ln(\dot{\varepsilon})} \tag{3}$$

Therefore, taking the slope of $\ln(\sigma)$ *versus* $\ln(\dot{\varepsilon})$ determines the strain rate sensitivity. The effect of strain rate on the fracture strength of W5|7 GB with the 9.4° misorientation angle is shown in Fig. 7. The higher the strain rate, the higher the strength of the material because there are fewer energy-dissipating mechanisms active in the given strain rates of up to 10^{-8} s^{-1}. Furthermore, fracture strength is more strain rate sensitive at higher temperatures than at low temperatures, but it saturates at $T \geq 200$ K. At higher strain rates, fracture strength is less temperature sensitive. At a temperature below 200 K, the fracture strength of monolayer WSe_2 GBs converges to the same value of $\ln(\sigma) \approx 3$ upon increasing the strain rate of $\ln(\dot{\varepsilon}) \approx 24.5$.

Although we found a linear relationship between the strain rate and fracture stress at temperatures less than 300 K, we

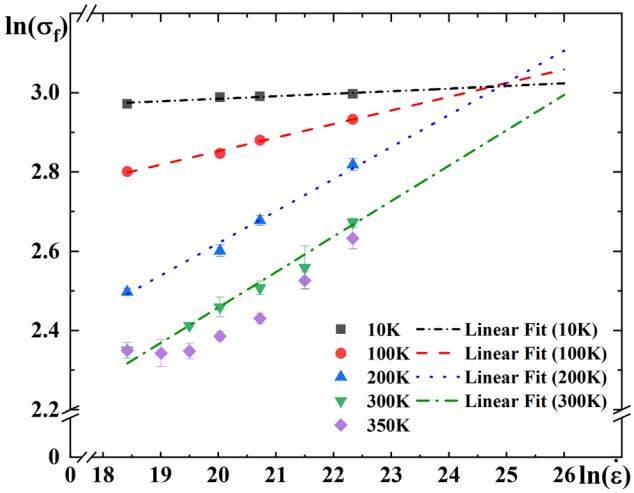

Fig. 7 Variation of fracture strength of 9.4° W5|7 GB with strain rate on a logarithmic scale. Low strain sensitivity is observed at low temp, which increases upon increasing temperature and a constant slope for $T > 200$ K.

revealed a nonlinear behaviour at the higher temperature of 350 K. The fracture stress reached a plateau at an elevated temperature below a critical strain rate, possibly due to the higher contribution of thermal fluctuations to the formation of initial microcracks, determining the final fracture stress. While thermal fluctuations will not have time to contribute to the formation of microcracks at low temperatures, resulting in dominated loading rate behaviour, at lower strain rates, the initiation of microcracks will be determined by thermal fluctuations and thus become independent of the loading rate.

Fracture process

The fracture mechanism of monolayer WSe_2 GB is quite different from that reported for the single atomic graphene GB. For graphene, the rupture process starts by breaking the bond shared by the hexagon–heptagon ring[56,63] since the initial stress was maximum for the same bond. However, the initial compressive stress for the WSe_2 5|7 dislocation is maximum for

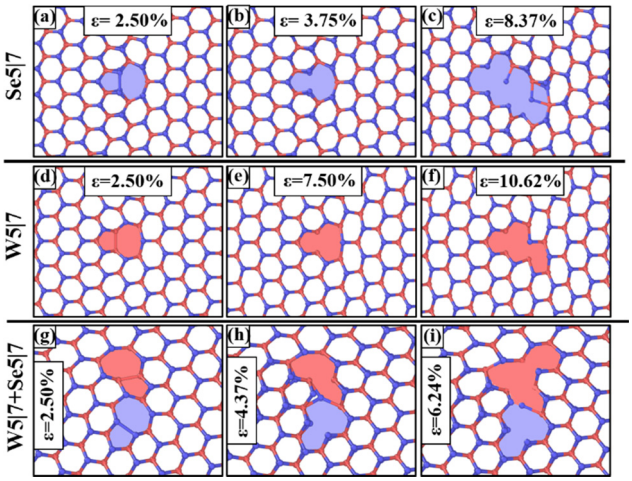

Fig. 8 Kinetics of fracture for bicrystal WSe_2 structures with different GBs. (a–c) 9.4° Se5|7, (d–f) 9.4° W5|7, and (g–i) 44.6° W5|7 + Se5|7. Snapshots are shown at different strains at 10 K temperature. W5|7 and Se5|7 dislocations in GBs are painted red and blue, respectively. Red circles represent W atoms, and blue circles represent Se atoms.

the bond shared by 5|7 rings (Fig. 8), that is, the Se–Se bond for Se5|7 GBs and W–W bond for W5|7 GBs; see Fig. 8(b), (e), and (h). Although these bonds are under compressive stress, they break first instead of the ones under tension, *i.e.*, single W atom of heptagon for Se5|7 GBs, double W atoms of the heptagon for W5|7 GBs. The Se–Se bond in Se5|7 GBs and W–W bond in W5|7 GBs cannot accommodate the external strains by bond rotation. Thus, although the pre-strained W–Se bond experiences the highest tensile stress, it still will not break as it can accommodate the external strain by rotating the W–Se bond, shown in Fig. S5 in the ESI.† The Se–Se bond in Se5|7 GBs breaks at a lower strain than the W–W bond in W5|7 GBs, which explains the higher failure strain for W5|7 AC tilt GB structures. Subsequently, the hexagon–heptagon ring dissociates, Fig. 8, and cracks spread quickly along the GBs, explaining the sudden drop in stress–strain curves.

Conclusions

The role of GB defects with varying misorientation angles on the mechanical properties of WSe_2 at different temperatures was investigated using MD simulations. W5|7 and Se5|7 AC tilt GBs with misorientation angles of 9.4°, 13.2°, and 21.8° and one W5|7 + Se5|7 ZZ tilt GB with misorientation angles of 39.4°, 44.6°, and 48.4° were studied within the 10 K to 300 K temperature range. Our results suggest that with increasing temperature, the fracture strength reduces for all the symmetric GB structures of WSe_2 due to the thermal activation of bond breakage and microcrack formation at higher temperatures. The effect of GB misorientation angle on fracture strength is noticeable at lower temperatures and reduced upon increasing temperature. The misorientation angle changes the bond length and the internal stress state of the GB atoms and, thus, the strength at which the material fails. We have shown that AC tilt W5|7 GBs have a higher fracture strength than AC tilt Se5|7 and ZZ tilt W5|7 + Se5|7 GBs. Furthermore, we revealed that the fracture strength of high angle ZZ tilt W5|7 + Se5|7 GBs decreases upon increasing the misorientation angle and become temperature insensitive. The Young's modulus of both AC and ZZ tilt GBs also reduced and reached a plateau upon increasing temperature. Furthermore, we investigated the sensitivity of our results to the strain rate, indicating insensitivity of the results for temperatures above 200 K. Also, the fracture strength of monolayer WSe_2 converged to a specific value for $T < 200$ K upon increasing the loading rate. The results presented here provide a fundamental understanding of the role of GBs in bi-atomic monolayers, such as TMDCs, on their final mechanical performance. Thus, it paves the way to design next-generation optoelectronic devices.

Author contributions

Nuruzzaman Sakib: methodology, investigation, formal analysis, visualization, writing – original draft, Shiddartha Paul: writing – review & editing, Nadire Nayir: writing – review & editing, Adri C. T. van Duin: writing – review & editing, Sara Neshani: writing – review & editing, Kasra Momeni: conceptualization, writing – review & editing, supervision, funding acquisition.

Conflicts of interest

There are no conflicts to declare.

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